

92 8. (Amended) The semiconductor light emitting device of claim 1 or 5,
wherein said active layer is a single quantum well structure or a multiple quantum well
structure.

93 35. (Amended) The growth method of claim 33, wherein the molar number of
said introduced Group IA element is larger than the molar number of said Group VIIB
element.

94 38. (Amended) The growth method of claim 36, wherein the molar number of
said introduced Group VB element is larger than the molar number of said Group IIIB
element.

95 53. (Amended) The semiconductor laser of claim 51, wherein said electric
current constriction layer is made of $Mg_zZn_{1-z}O$ ($0 \leq z < 1$).

REMARKS

By this Amendment, claims 4, 7, 8, 35, 38 and 53 are amended to delete
improper multiple dependency. No new matter is contained in the amendments.

These amendments are being made under 37 C.F.R. 1.121 as amended. A copy
of the claims marked-up to show the amending is attached.